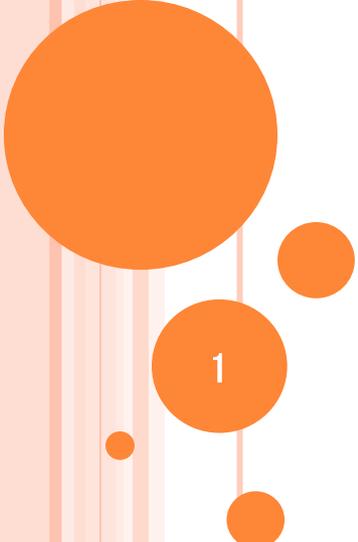


# DEVELOPMENT OF SRF GUN APPLYING NEW CATHODE IDEA USING A TRANSPARENT SUPERCONDUCTING LAYER



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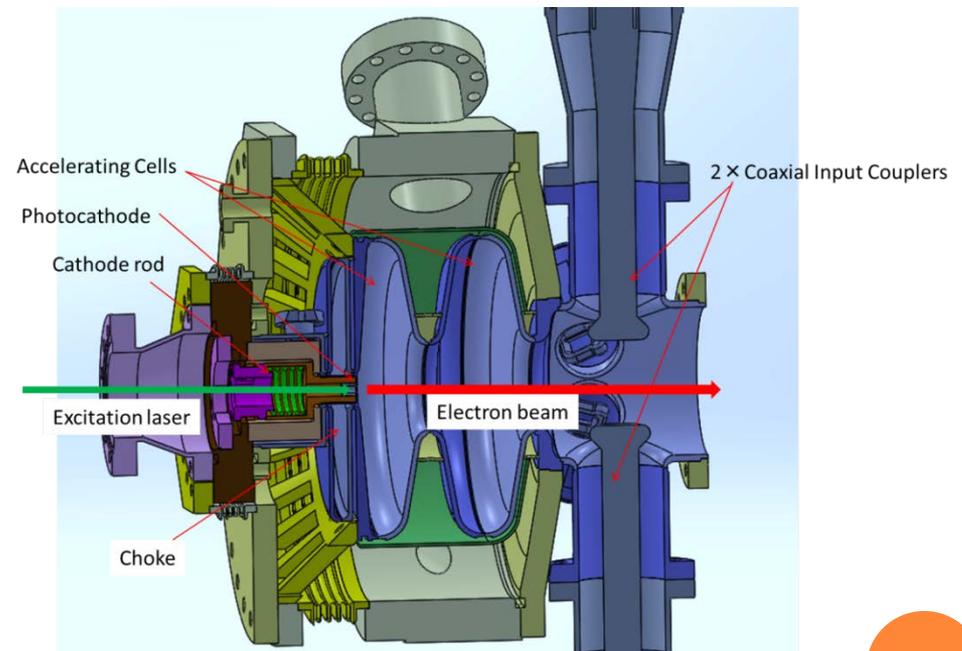
## **5. Summary**

# 1-1 Target of the KEK SRF gun

- KEK Started SRF gun development for future linac base accelerator.
- 3 GeV KEK- ERL was selected as the target parameters to simulate the gun design.
  - Target parameters are same as KEK ERL DC gun.
- Key point is back side excitation structure.

## Target parameters (KEK-ERL)

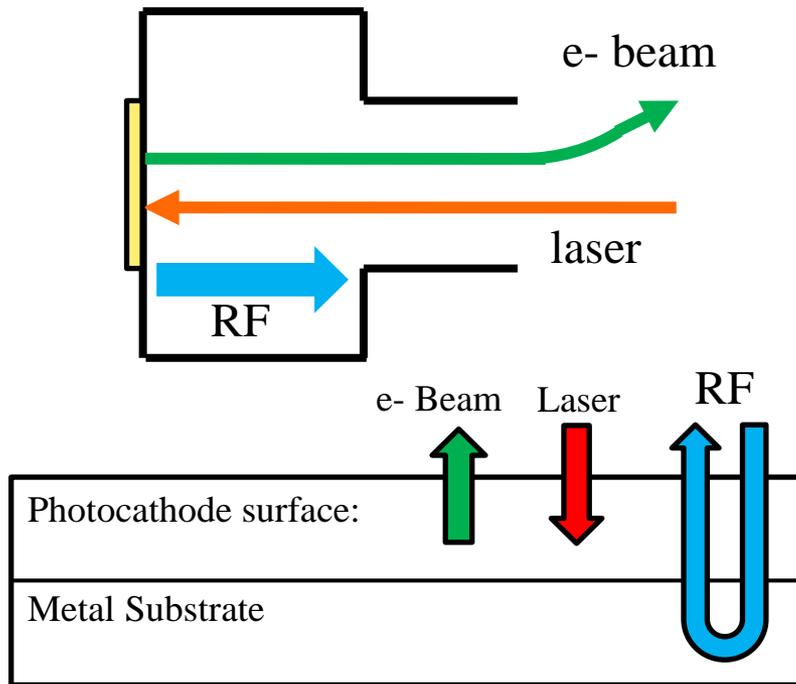
Parameters	Value
RF frequency	1.3 GHz
Beam energy	2 MeV
Current	100 mA
Bunch length (rms)	3 ps
Bunch charge	77 pC
Repetition frequency	1.3 GHz
Normalized emittance	$< 1\pi$ mm mrad
Energy Spread	$< 0.1\%$



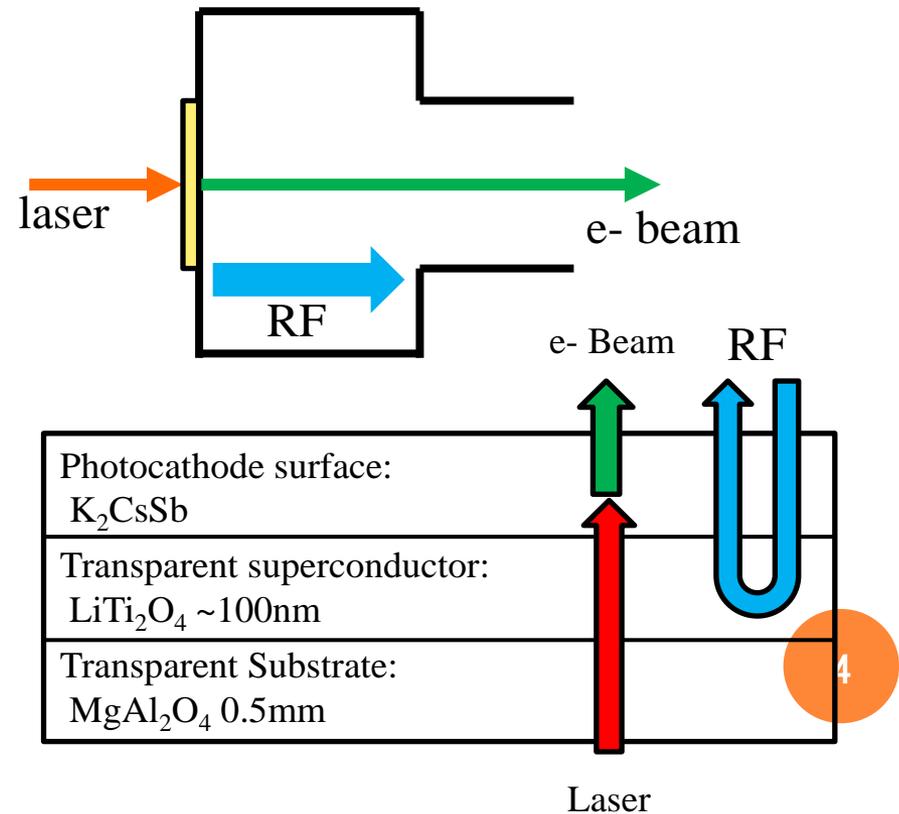
# 1-2 Design concept of the KEK SRF gun

- Merits of back side excitation
  - Simple RF cavity and beam line structure.
  - Laser control could be more precisely.
    - Laser 3D distribution control is necessary for low emittance beam.
- We propose a photocathode structure using transparent superconductor.
  - The superconductor protects transparent substrate from RF damage
  - RF leakage from photocathode can be blocked and surface electric field on the photocathode can be kept high.

(a) Front side excitation



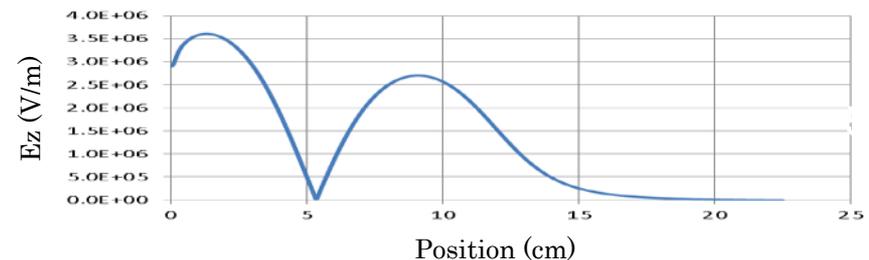
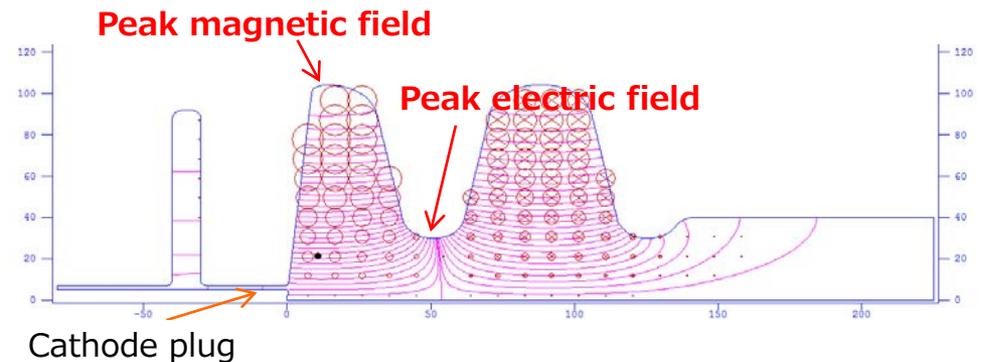
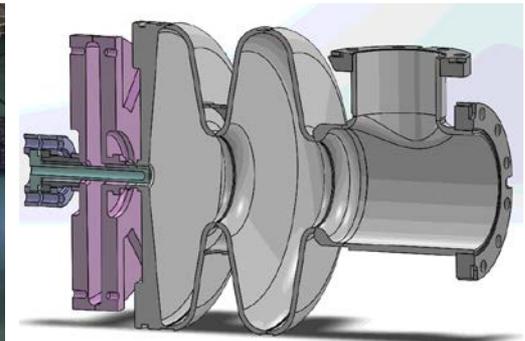
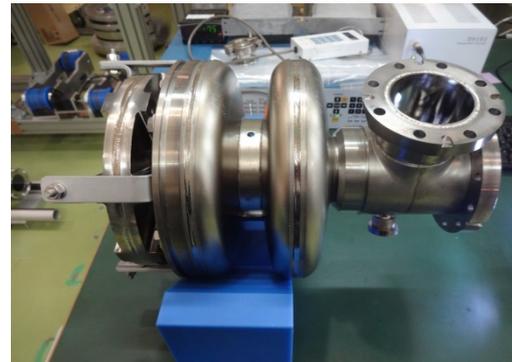
(b) Back side excitation



# 2-1 RF parameters

- KEK SRF gun #1 was designed to check basic RF parameters (maximum  $E_{sp}$ ,  $Q_0$ ).
- Cavity was designed by SUPERFISH and GPT.
  - Slope of the cavity was designed to compensate the space charge effect.
- Target  $Q_0$  values are estimated from ILC target.

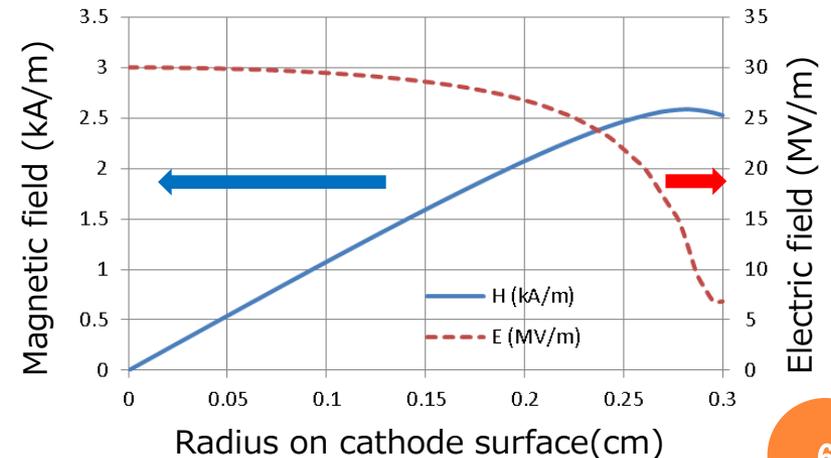
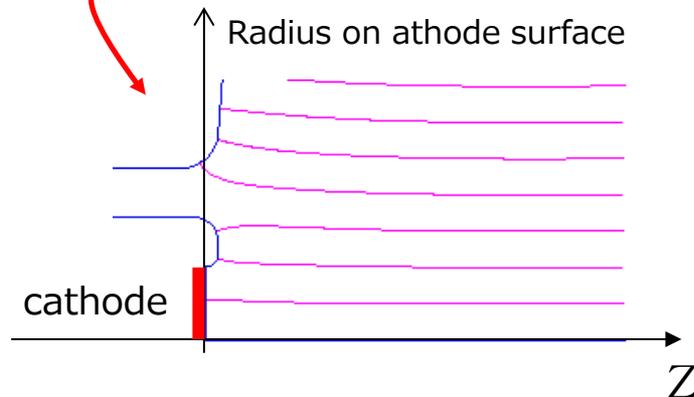
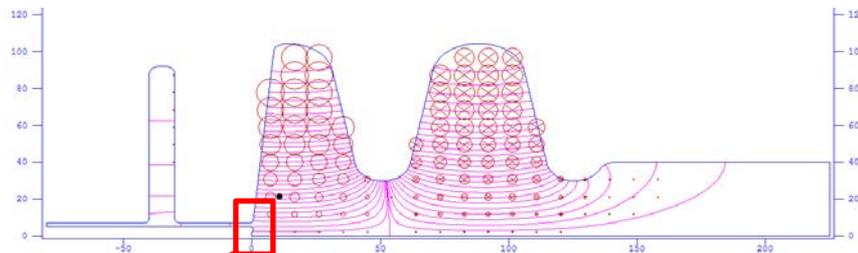
Parameter	Value
<b>Beam energy</b>	<b>2 MeV</b>
<b>Projected emittance</b>	<b>0.6 n mm.mrad</b>
<b>Projected energy spread</b>	<b>0.09%(1.84 keV)</b>
<b>Peak electric field</b>	<b>41.9 MV/m</b>
Peak magnetic field	95.2 mT
RF phase	55°
Geometrical Factor	135.6 $\Omega$ (TESLA 270 $\Omega$ )
Target surface resistance	30 n $\Omega$ (ILC target)
Target Q value	4.5 $\times 10^9$
Target cavity loss	8 W



# 2-1 RF parameters on photocathode

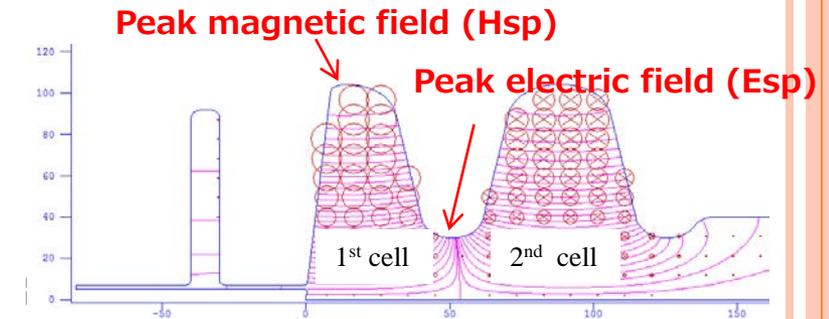
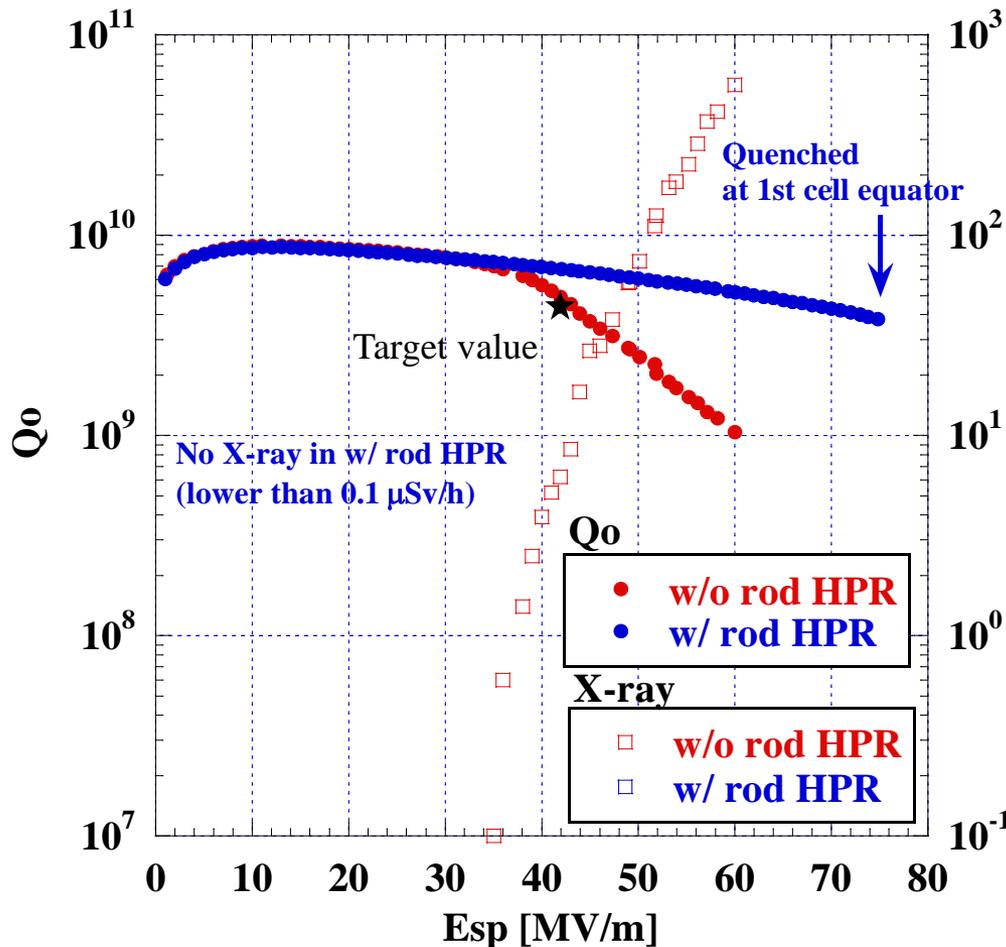
- Peak electric on the photocathode is 70% of iris peak electric field.
- RF critical magnetic field of the photocathode should be higher than 2.6 kA/m (3.3 mT).
  - It is enough smaller than niobium. Niobium is  $\sim 2000$  mT at 2K
- High gradient tests (Vertical tests) were done with dummy cathode rod.
  - Dummy cathode rod was shaved out from bulk niobium and doesn't have the cathode mount structure.

Dummy cathode rod made of niobium



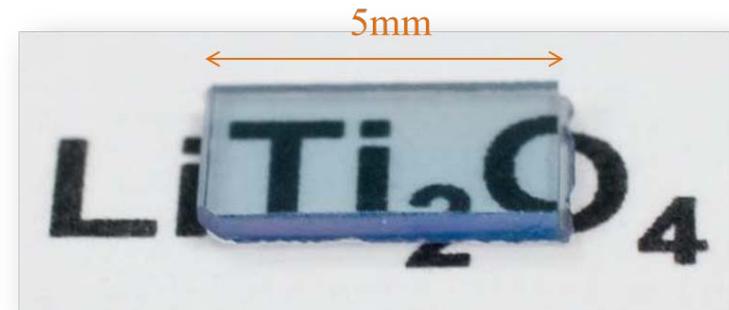
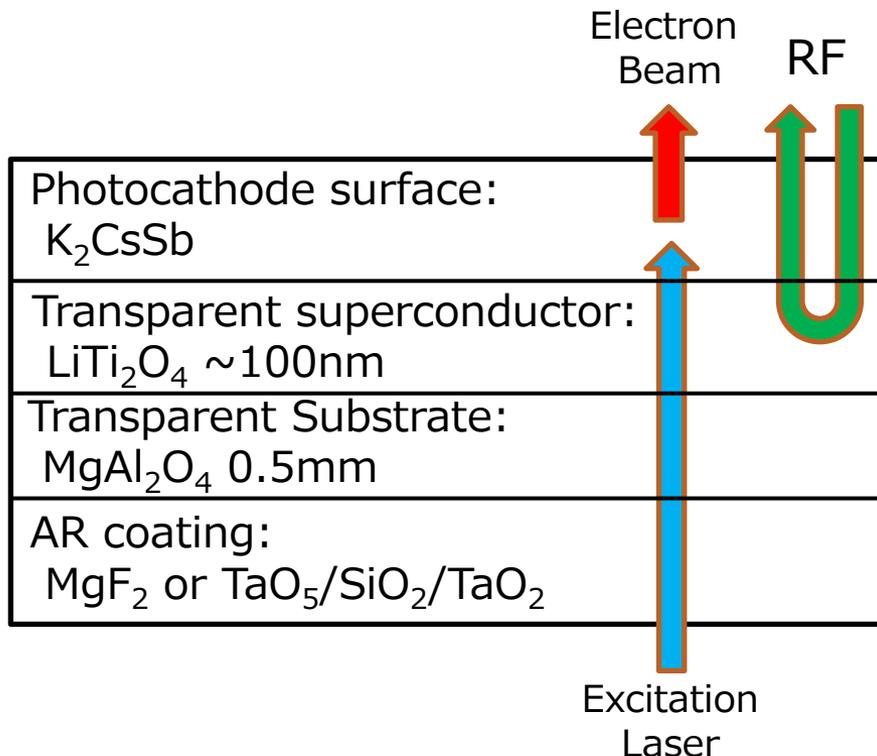
# 2-2 Vertical test results

- The cathode plug cleaning is important to achieve high gradient
- The peak surface electric field reached 75 MV/m and X-ray couldn't be observed with HPR.
- However HPR should not apply to the transparent superconductor cathode substrate because it is very thin and delicate.
  - We have to search other method for cleaning for example hydrogen cleaning or sputtering.



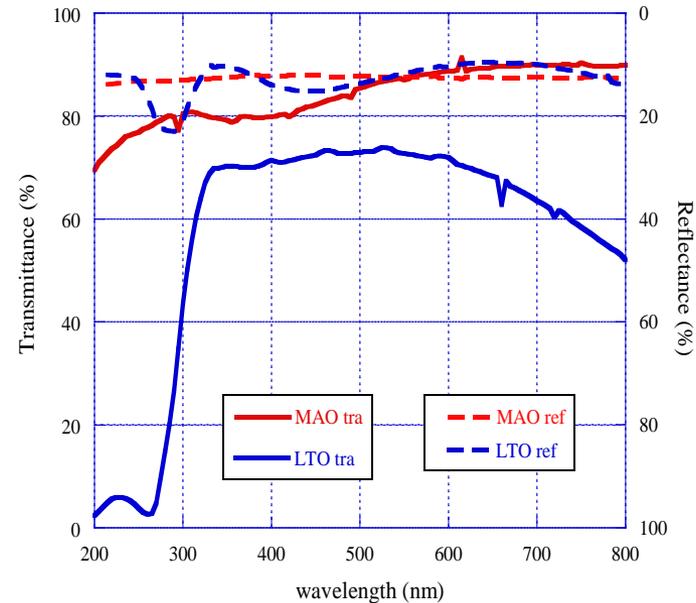
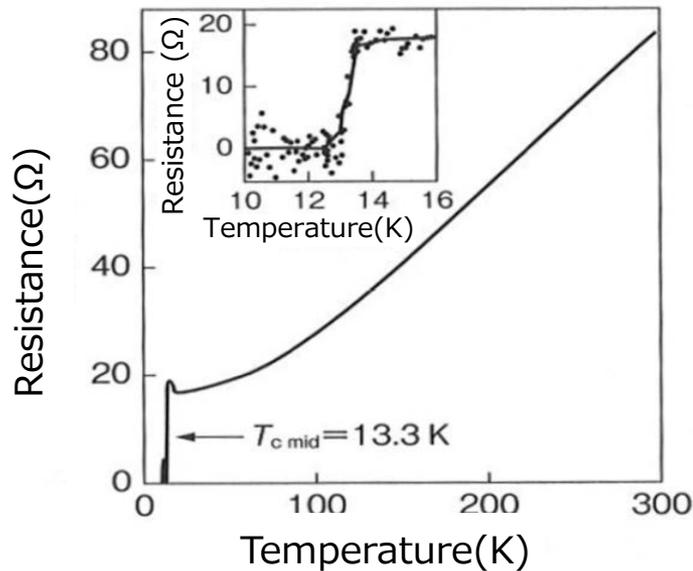
# 3-1 Concept of the photocathode.

- There are 4 layers in the photocathode.
  - Photocathode surface is  $K_2CsSb$ .
    - The lattice constant of  $K_2CsSb$  (0.861 nm) is close to  $LiTi_2O_4$  (0.8405 nm).
  - The transparent superconductor  $LiTi_2O_4$  can block the RF leakage and transmit the excitation visible light at the same time
  - $MgAl_2O_4$  is the substrate for epitaxial growth of  $LiTi_2O_4$ .
  - AR coating is a option for increasing laser efficiency.
- The photocathode performances are evaluated by quantum efficiency, initial emittance and critical DC magnetic field.

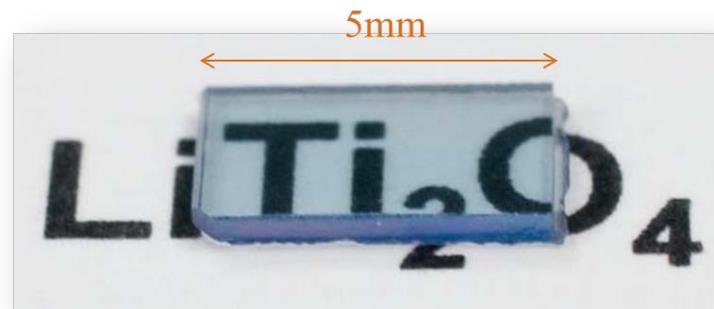


# 3-1 Transparent superconductor

- Transition temperature is  $\sim 13\text{K}$ . Transmittance is 75% at 530nm.
- We will apply AR coating to decrease the reflection.  
 $\Rightarrow$  We will use the  $\text{MgF}_2$  or  $\text{TaO}_5/\text{SiO}_2/\text{TaO}_2$  layer.



Parameter	Value
Tc mid	13.3 K
Resistivity	$3.3 \times 10^{-4} \Omega\text{cm}$ (at R. T.)
Lattice constant	$a_{LTO} = 0.8405 \text{ nm}$
Transmittance	75 % (at 530 nm)
Carrier density	$1.1 \times 10^{22} \text{ cm}^{-3}$
Hall mobility	0.8 (280K), 6.0 (15K) $\text{cm}^2\text{V}^{-1}\text{S}^{-1}$



# 3-2 Photocathode development chambers

## Quantum efficiency

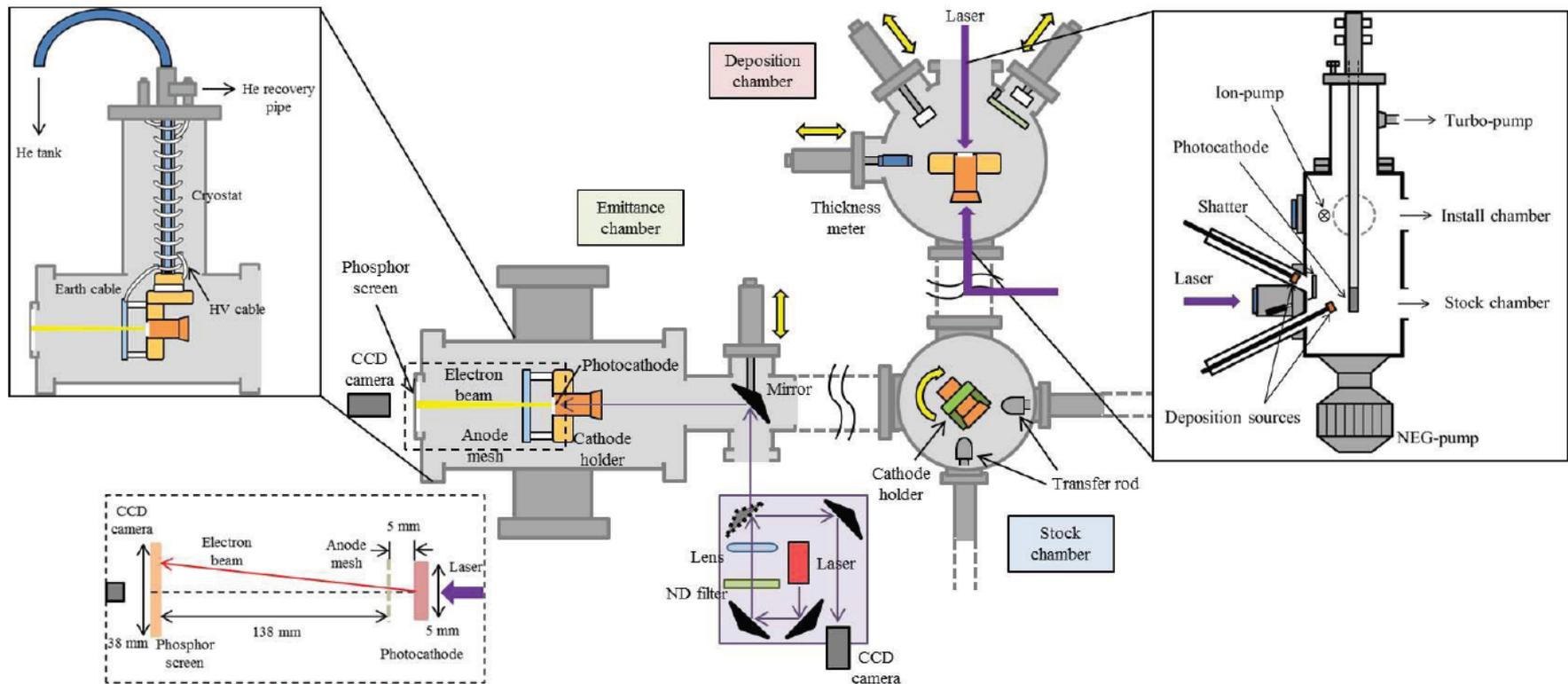
- QE was measured at deposition chamber.
- Xenon lamp were used to measure QE spectrum.
- Excitation light can be inject from back and front. Transmittance can be measured.

## Initial emittance measurement

- The photocathode can be cooled down to 7 K.

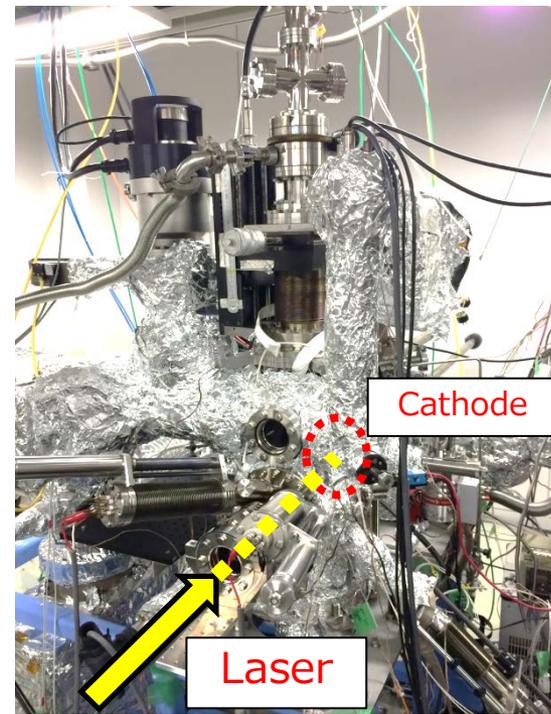
## Critical magnetic field

- Take out from chamber and measured by SQUID MPMS7 (Quantum Design, Inc.)

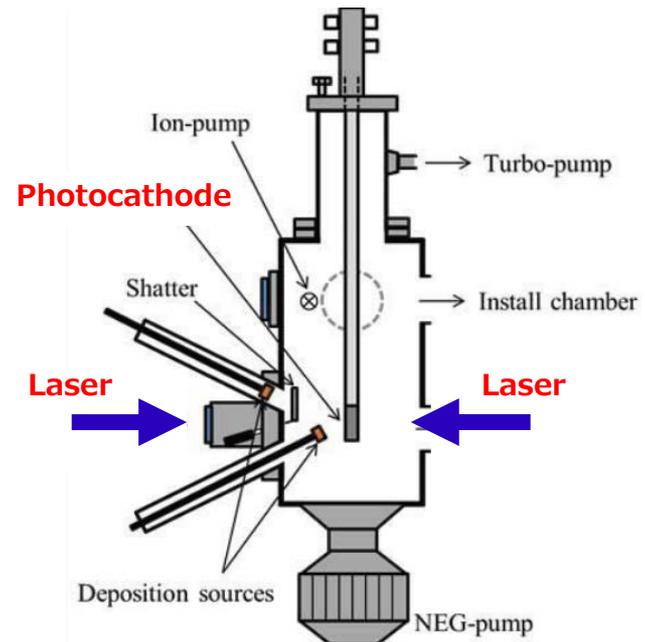


# 3-3 Photocathode deposition

- The photocathode deposition chamber has cesium (SAES), potassium (SAES) and bulk antimony evaporation sources.
- Laser and xenon lamp can inject from front and back side of the photocathode.
- The chamber vacuum is  $6 \times 10^{-8} \sim 1 \times 10^{-7}$  Pa during the deposition.
- Base pressure is  $1 \times 10^{-8}$  Pa.

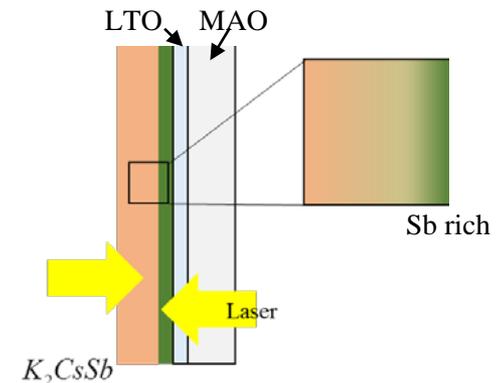
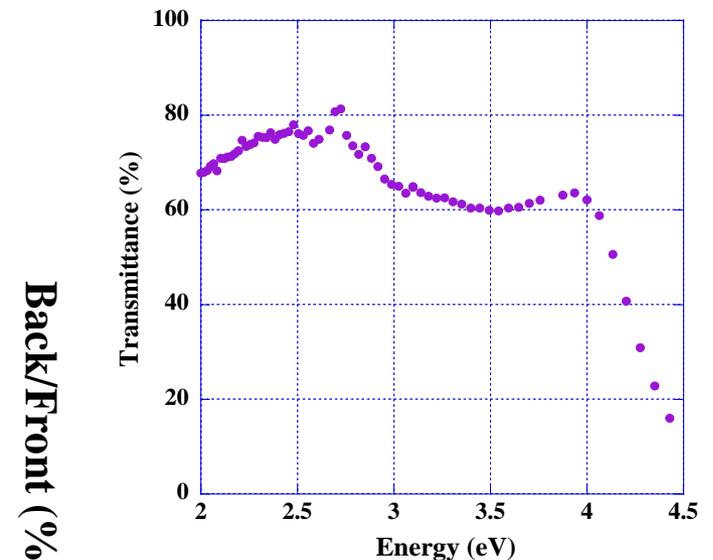
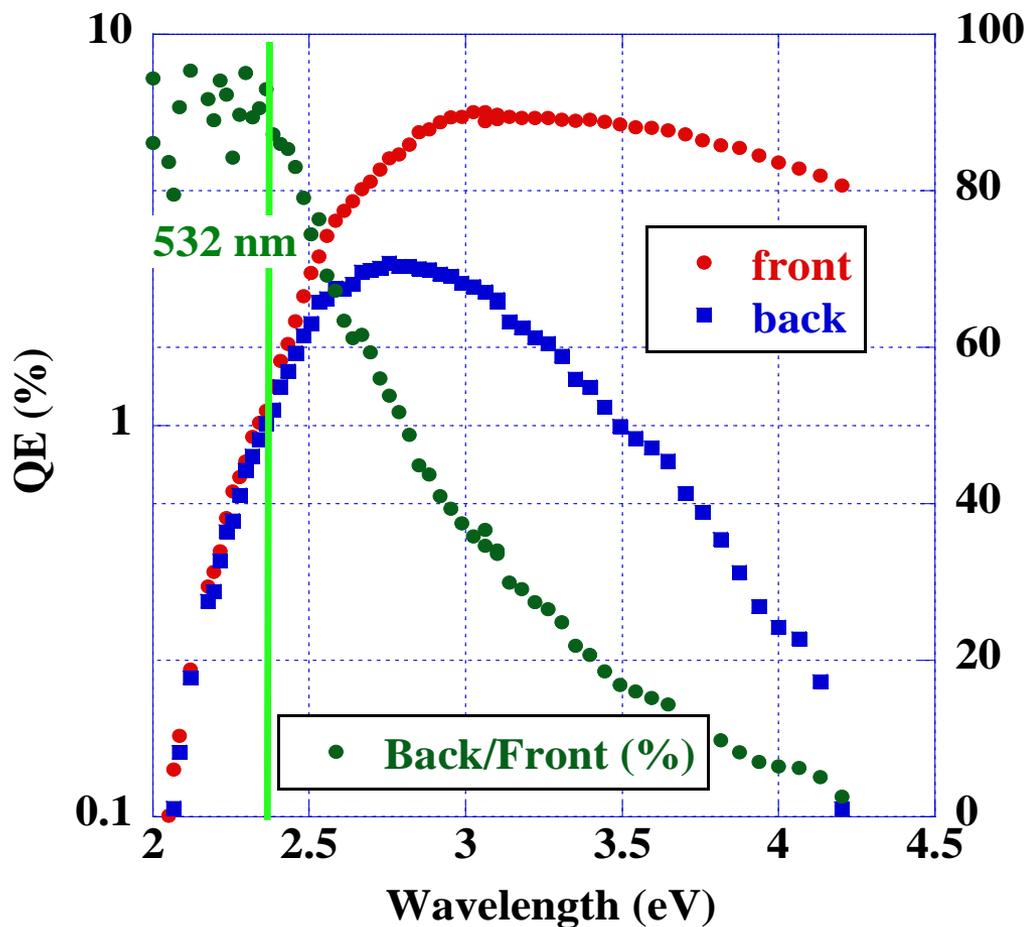


Procedure	Condition
Heat cleaning	$\sim 500$ °C x 3 hours
Sb deposition	150°C , Thickness 10nm (Transmittance decrease to 20-30%)
K deposition	$\sim 120$ °C, QE peak
Cs deposition	100 °C, QE peak



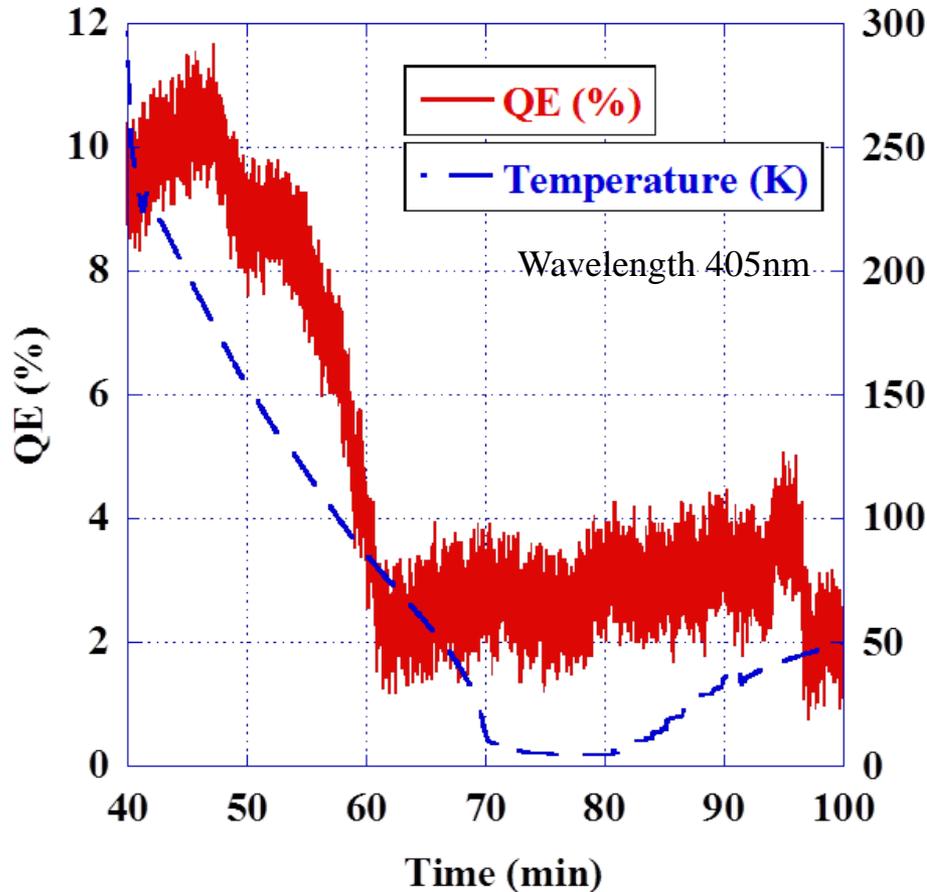
# 3-3 Quantum efficiency

- The threshold energy is  $1.85 \pm 0.15 \text{ eV}$ . This is same value as other studies.  
⇒ K<sub>2</sub>CsSb deposition on the transparent superconductor was successful.
- The ratio of back side and front side QE can't be explain by the transmittance of LTO.  
⇒ We suspect Sb rich layer exists on the boundary.
- But It is not a problem for gun operation because we will use 532nm laser.
  - At 532nm, back side QE is 90% of the front side.

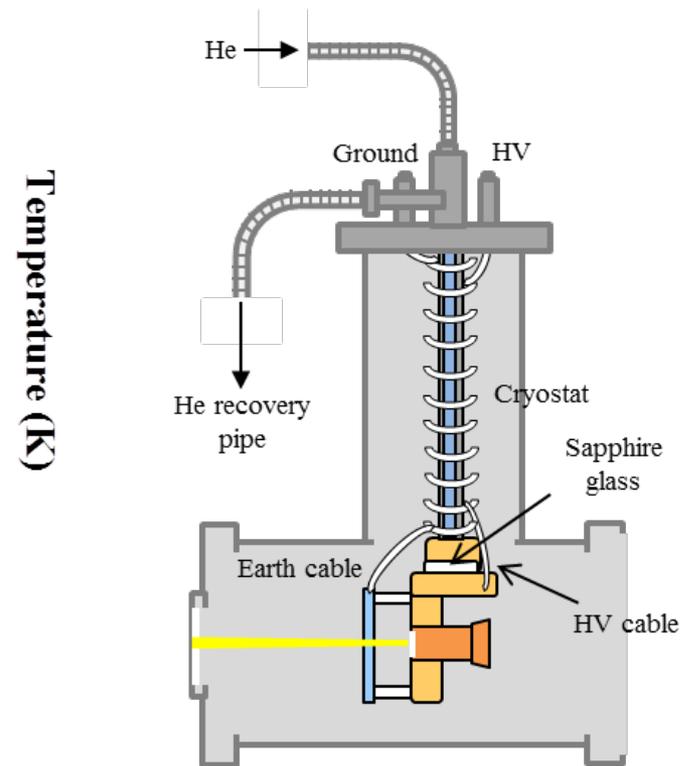


# 3-3 Quantum efficiency at low temperature

- Photocathode was transferred to initial emittance chamber which has a LHe small cryostat.
- QE was decreased during cooling.
  - We suspect residual gas was absorbed on the photocathode surface and increase the surface work function.
- Further study of photocathode performance at cryogenic temperatures and ways to improve this performance is essential for the photocathode development.



Initial emittance chamber

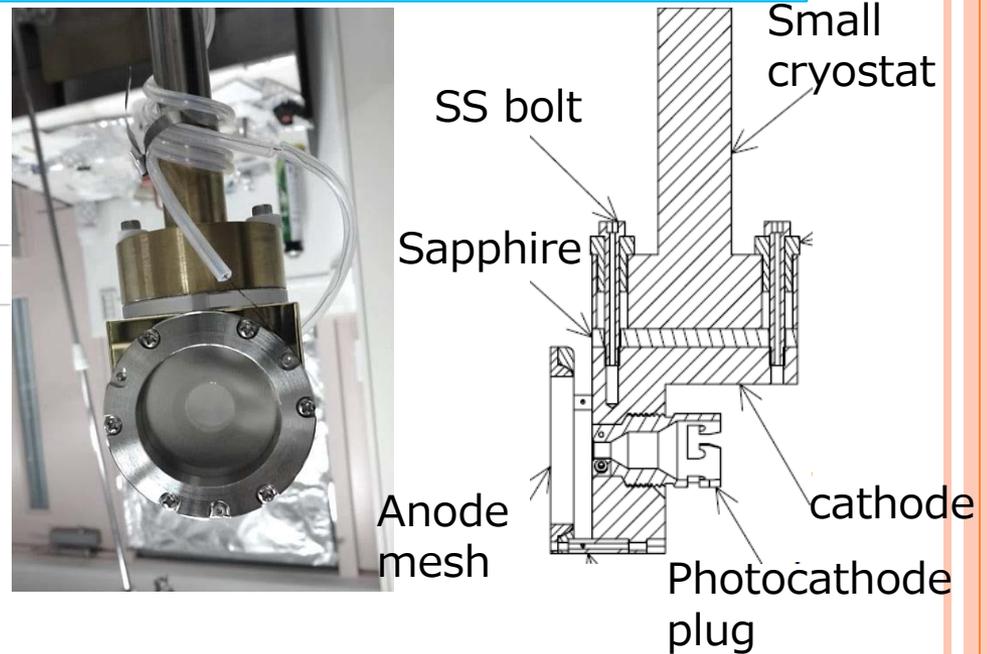
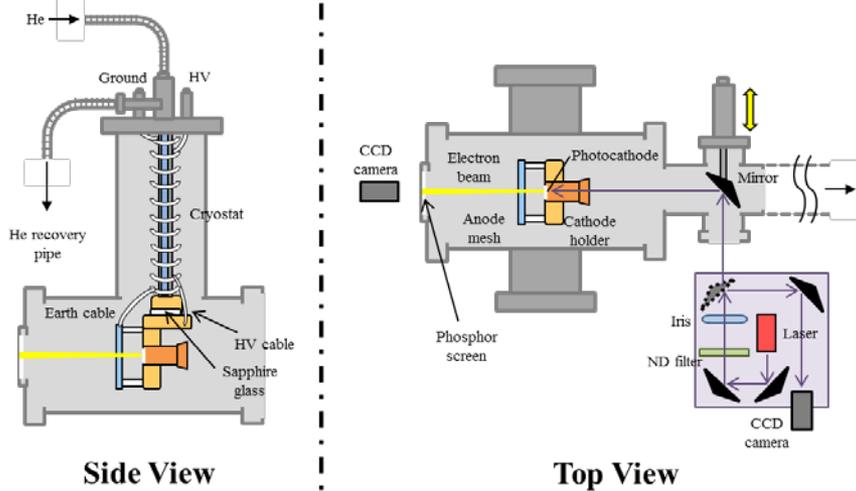


chamber pressure:  $3.6 \times 10^{-8}$  Pa

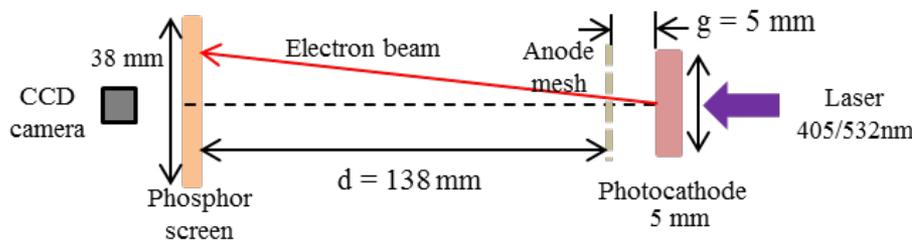
# 3-4 Initial emittance

- Initial emittance was calculated by measuring the expansion of beam size.
- Parallel plate DC gun consists of thin anode mesh and cathode block.
- Laser was inject from backside of the photocathode. laser spot side is  $\Phi \sim 0.1\text{mm}$

Initial emittance chamber scheme



Initial emittance measurement scheme and equation



$$\frac{\epsilon_n}{\sigma_x} = \frac{1}{2g + d} \cdot \sqrt{\frac{2eV}{mc^2}} \cdot \langle r^2 - \sigma_x^2 \rangle^{1/2}$$

Labels for the equation:
 

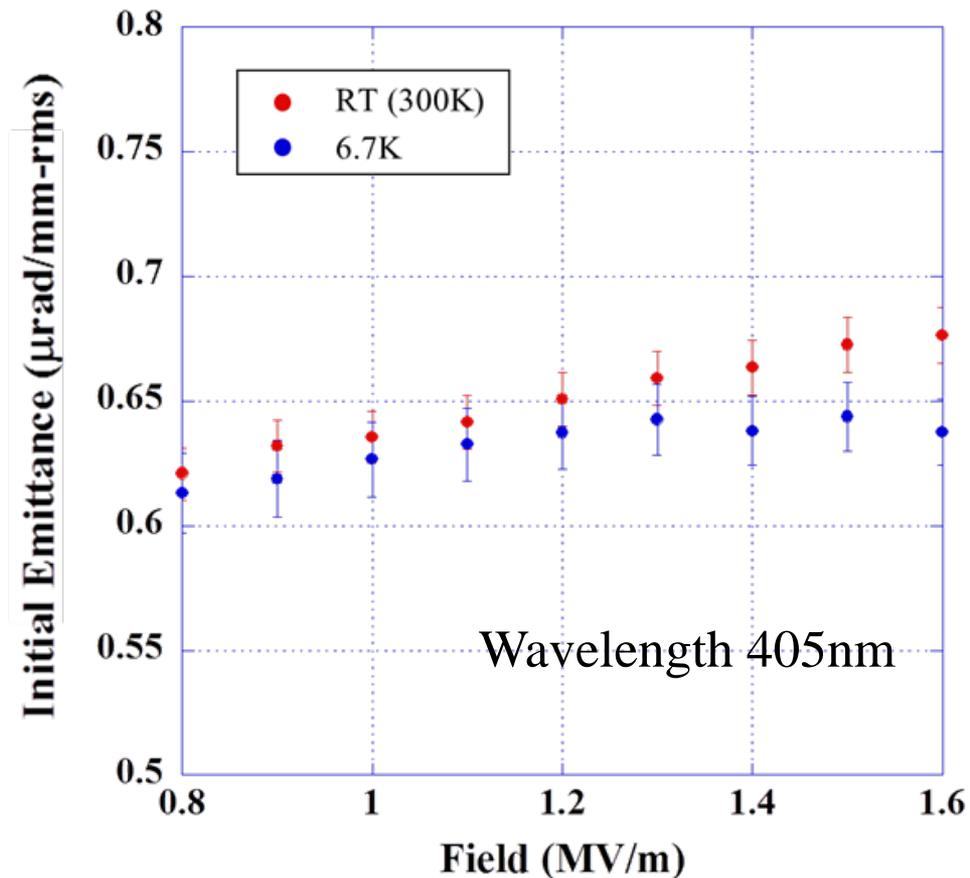
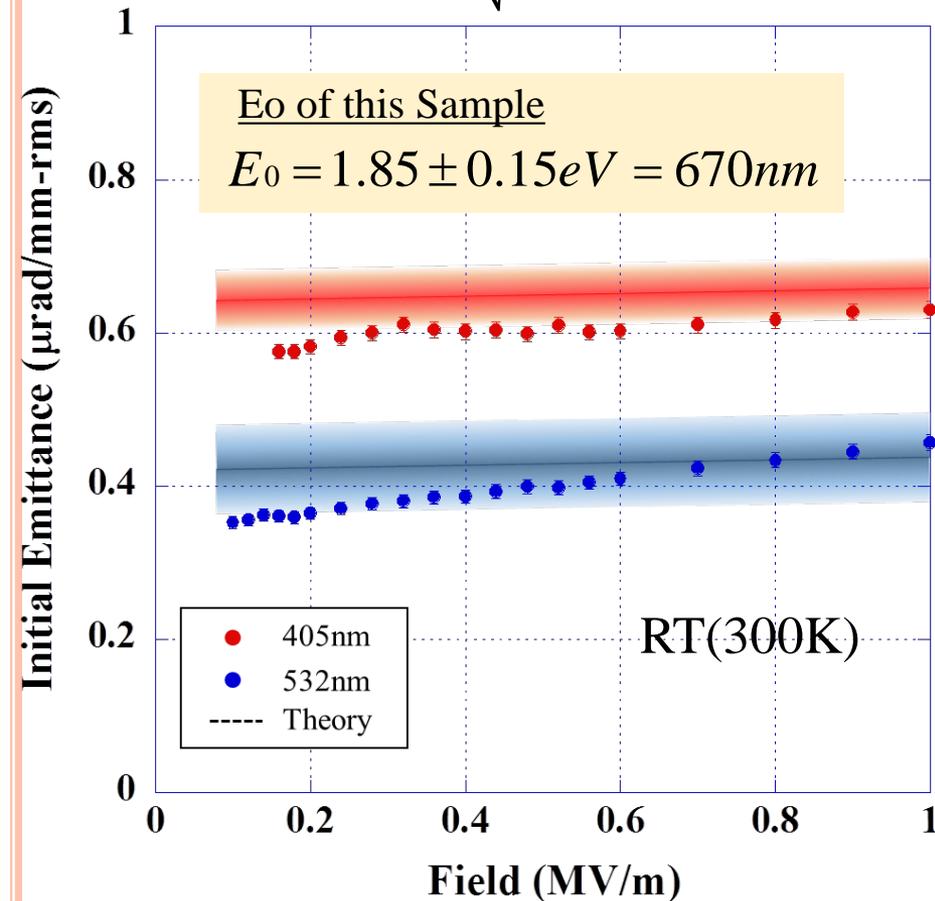
- Gap voltage (kV) points to  $2eV$
- Beam radius points to  $\langle r^2 - \sigma_x^2 \rangle^{1/2}$
- Laser radius points to  $\sigma_x^2$

# 3-4 Initial emittance

- The measurement results at RT almost agree with theory.
- Initial emittance should be constant regardless of the electric field
  - The measured data is rising along with electric field.
  - We suspect anode was bended with electric field, because it is 20  $\mu\text{m}$  thin film.

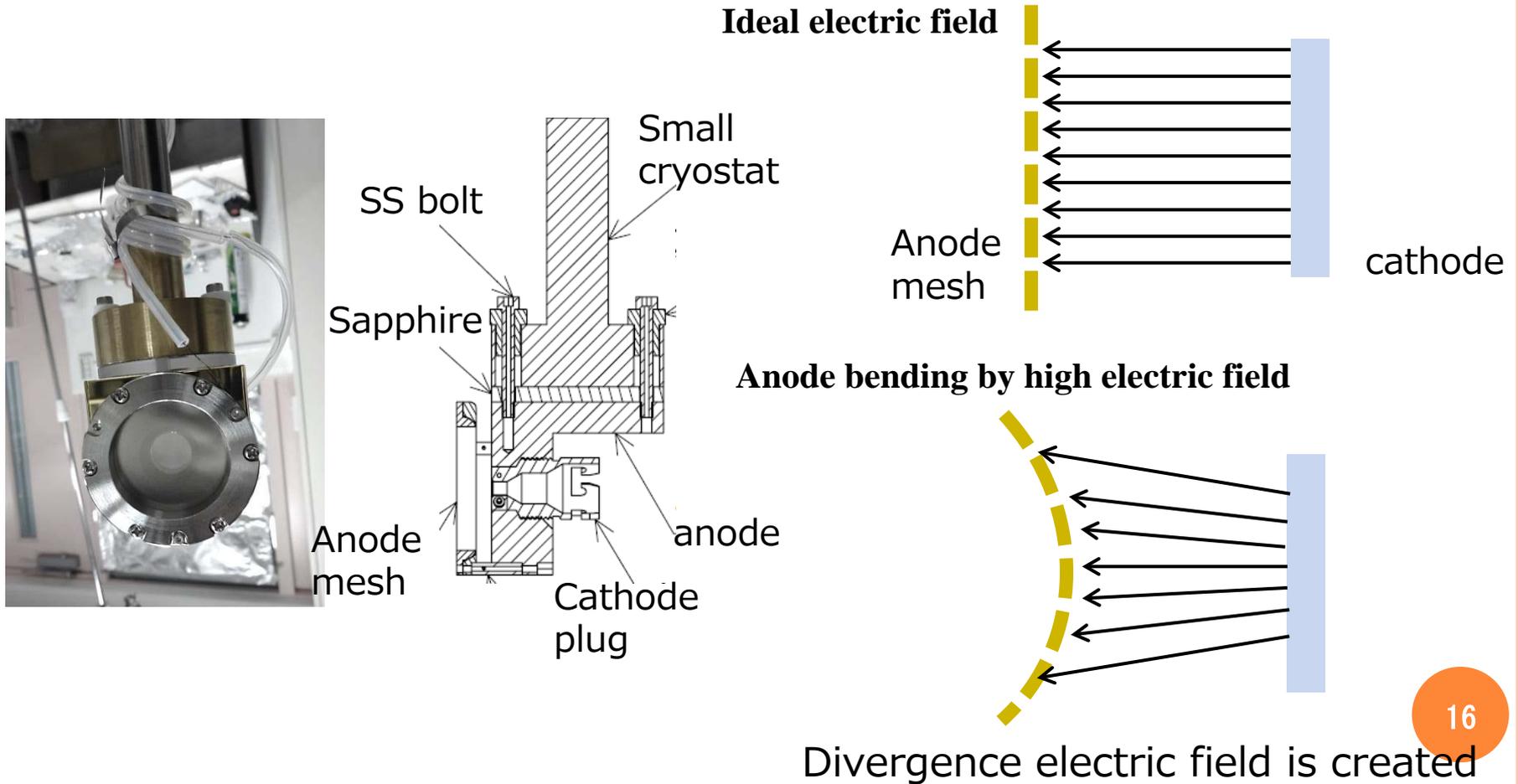
Theory: 
$$\varepsilon_n = \frac{R}{2} \sqrt{\frac{2(\hbar\omega - E_0 + \phi_{sch})}{3mc^2} + \frac{2k_B T}{mc^2}}$$

Shottky effect: 
$$\phi_{sch} = \sqrt{\frac{eV}{4\pi\varepsilon_0}}$$



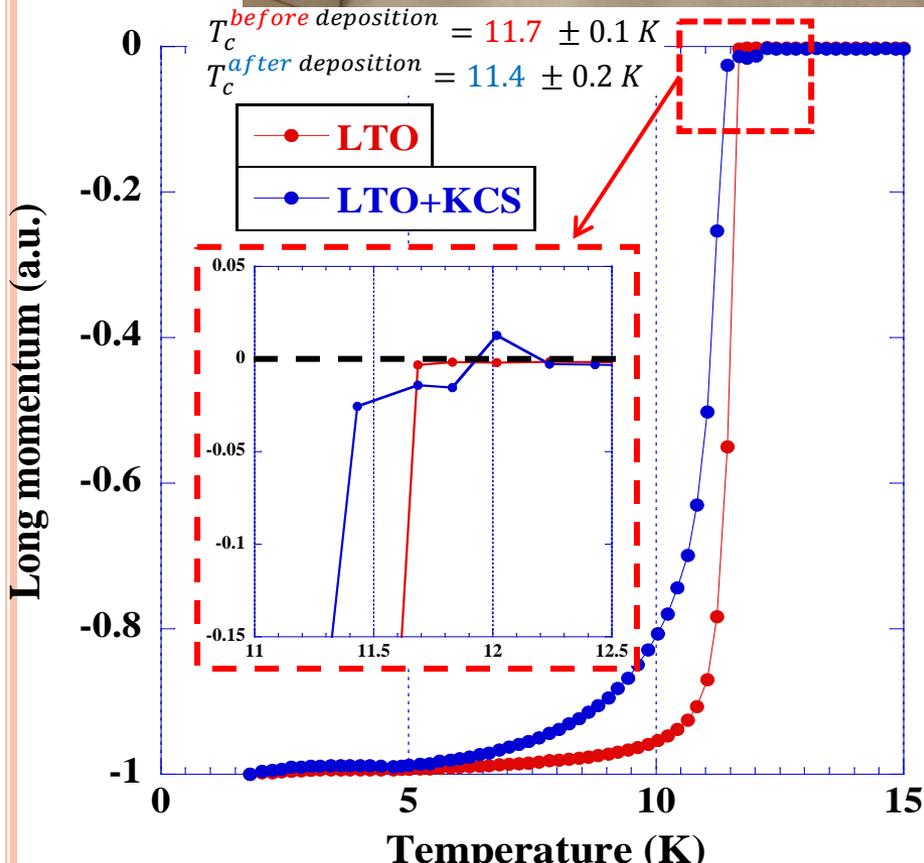
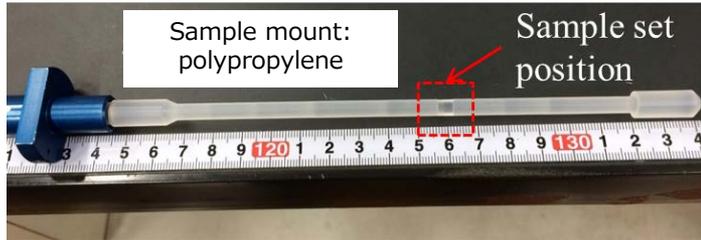
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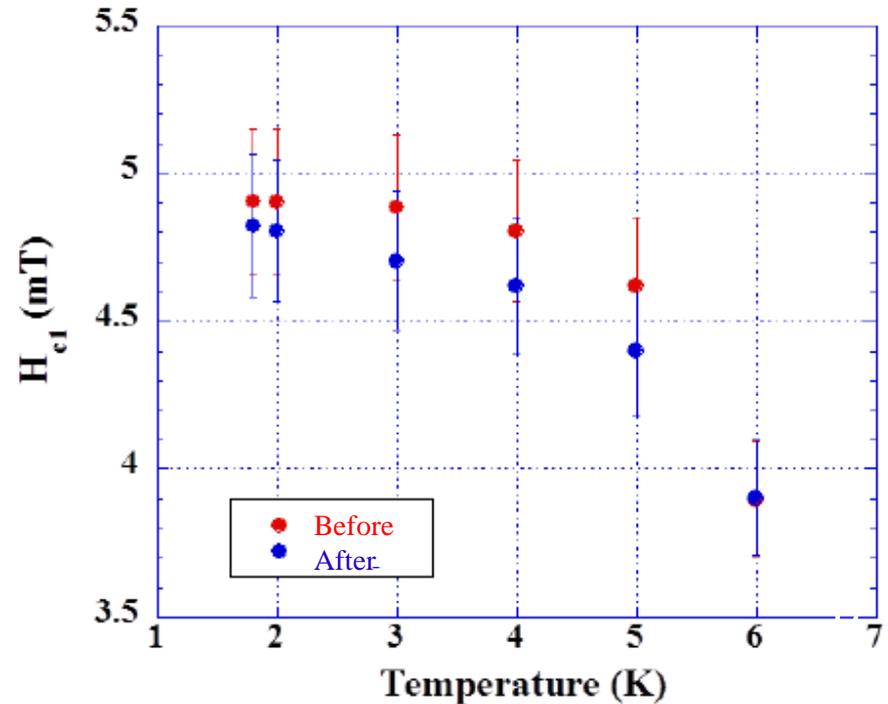


# 3-5 Critical magnetic field

- The critical temperature and critical magnetic field were not changed before and after  $K_2CsSb$  devotio.
- Critical magnetic field is higher than the SRF gun operation.



Target RF magnetic field is 3.3mT



# 5 Summary

- KEK SRF gun has been developed for 3GeV KEK ERL
  - Prototype #1 cavity was designed to check the RF parameters.
    - Target  $E_{sp}$  is 42 MV/m, it correspond to  $E_{acc} = 20\text{MV/m}$  of TESLA cavity.
    - The peak surface electric field reached 75 MV/m and X-ray couldn't be observed with HPR.
- 
- We have to search other method for cleaning because  $\text{LiTi}_2\text{O}_4$  is thin and delicate.
  - Properties of the transparent photocathode with transparent superconductor were measured.
    - QE ratio of back side and front side was 90% at 532 nm.
    - Initial emittance almost agreed with theory.
    - Critical magnetic field satisfy the SRF gun operation.
    - QE decrease during cooling down.
    - Further study of photocathode performance at cryogenic temperatures and ways to improve this performance is essential for the photocathode development.

Thank you for your attention !